Appl No. 10/679,787

Amdt. dated Jan. 16, 2006

Reply to Office action of Oct. 14, 2005

Remarks/Arguments:

Applicant thanks Examiner Johnson for his clear explanation of the claim rejections and his response to applicant's argument filed on August 31, 2005. In response to the Office action of October 14, 2005, applicant cancels additional claims 12-31 and inserts new claims 32 and 33. The new claims are fully supported by the original specification and the original drawings. And they distinguish over the cited references:

Claim 32

Claim 32 includes a two-layered copper structure with one layer being about $0.6 \mu m$ thick. Further, this structure has a nickel layer sandwiched between and contacting both copper layers. This combination is not disclosed or suggested in any of the references.

Claim 33

Claim 33 properly depends on claim 32 with additional limitation that during a reflow process, the copper in the about $0.6 \mu m$ thick layer combines with tin from the solder ball to form a layer of Cu_6Sn_5 . This combination is not disclosed in the references as well.

Therefore, applicant respectfully requests further examination of this application and timely allowance of all pending claims.

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Respectfully submitted,

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Attorney for Applican

Rea No 152 305